

SBR10U150CT SBR10U150CTF SBR10U150CTI SBR10U150CTB

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I _{F(AV)} Rectangular Waveform	10	Α
V_{RRM}	150	٧
V _F @5A, Tj=125 ^O C	0.60	V, typ
Tj (operating/storage)	-65 to 175	°C

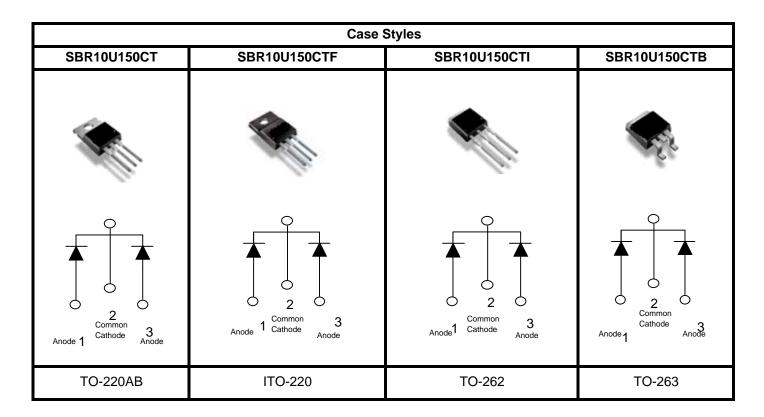
Device optimized for high temperature Power Supply applications

ELECTRICAL:

- * Ultra-Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, Fast Switching Capability
- * 175°C Operating Junction Temperature

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages





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Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified) SYMBOL **UNITS** DC Blocking Voltage V_{RM} Working Peak Reverse Voltage V_{RWM} 150 Volts Peak Repetitive Reverse Voltage V_{RRM} Average Rectified Forward Current (Rated V_R-20Khz Square Wave) - 50% duty 10 I_{\circ} **Amps** cycle Peak Forward Surge Current - 1/2 60hz 150 I_{FSM} **Amps** Peak Repetitive Reverse Surge Current 3 **Amps** I_{RRM} (2uS-1Khz) Instantaneous Forward Voltage (per leg) Тур Max $I_{\rm F} = 5A; T_{\rm J} = 25^{\circ}C$ 0.79 --- V_{F} Volts $I_F = 10A; T_J = 25^{\circ}C$ 0.88 $I_F = 5A; T_J = 125^{\circ}C$ 0.63 Maximum Instantaneous Reverse Current at Max Typ Rated V_{RM} I_R^* 0.2 mΑ $T_J = 25^{\circ}C$ 25 mΑ $T_{J} = 125^{\circ}C$ Maximum Rate of Voltage Change 10,000 dv/dt V/uS (at Rated V_R) Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263 2 °C/W $R\theta_{JC}$ Package = ITO-220 οС $T_{\rm J}$ -65 to +175 Operating and Storage Junction Temperature

 $^{^{\}star}$ Pulse width < 300 uS, Duty cycle < 2%



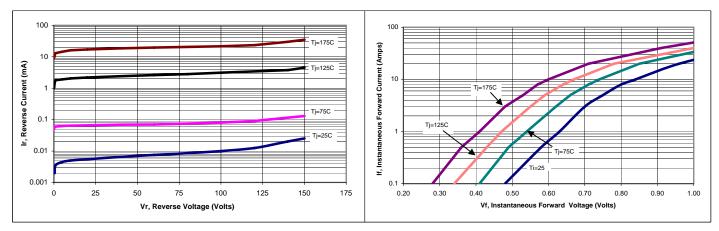


Figure 1: Typical Reverse Current

Figure 2: Typical Forward Voltage

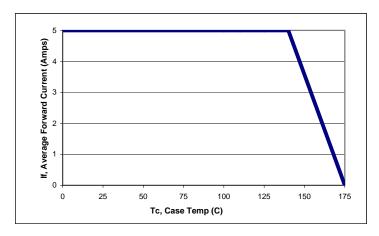


Figure 3: Current Derating, Case

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